

- Sub B1
A1
1. (Amended) A low impedance band-gap reference circuit, comprising:
- a band-gap reference circuit;
 - a buffer circuit electronically coupled with said band-gap reference circuit; and
 - a voltage pull-up device electronically coupled with said band-gap reference circuit and said buffer circuit, wherein said voltage pull-up device acts to reduce a required supply voltage to maintain a band-gap reference voltage and wherein said voltage pull-up device is implemented as a transistor with less than 1.0 VBE.

- Sub B1
A2
7. (Amended) An electronic device, comprising:
- a silicon substrate;
 - electronic circuitry constructed in said silicon substrate; and
 - a band-gap reference circuit electronically coupled in said electronic device, wherein said electronic circuitry requires reference to the output voltage of said band-gap reference circuit and said band-gap reference circuit is enabled for low impedance by a buffer circuit comprising a transistor with less than 1.0 VBE.

Sub B1
A3

(Amended) An electronic device as described in Claim 7, wherein said transistor with less than 1.0 VBE is connected as an emitter follower.

- Sub B1
A4
16. (Amended) In an electronic device, a method for providing a reference voltage, comprising:
- flowing current through an electronic element such that the band-gap voltage of said electronic element provides said reference voltage;
 - providing a buffer circuit enabled to provide low impedance; and
 - adjusting the voltage across said buffer circuit so that said band-gap reference voltage is maintained, wherein said voltage is a VBE OF LESS THAN 1.0 V.